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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.		
09/939,773	08/28/2001		ATTORNET BOCKET NO.	CONFIRMATION NO.	
	00/20/2001	Koji Kikuchi	SON-2192	3157	
23353 75	590 06/11/2003				
RADER FISHMAN & GRAUER PLLC					
LION BUILDING			EXAMINER		
1233 20TH STREET N.W., SUITE 501			COLEMAN, WILLIAM D		
WASHINGTO	N, DC 20036	,			
			ART UNIT	PAPER NUMBER	
			2823		
			DATE MAILED: 06/11/2003		

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application No.	Applicant(s)			
Office Action Summary		09/939,773	KIKUCHI, KOJI			
		Examiner	Art Unit			
		W. David Coleman	2823			
Period f	The MAILING DATE of this communication app or Reply	ears on the cover sheet with the	correspondence address			
- External control con	MORTENED STATUTORY PERIOD FOR REPLY MAILING DATE OF THIS COMMUNICATION. Insistons of time may be available under the provisions of 37 CFR 1.13 SIX (6) MONTHS from the mailing date of this communication. It is period for reply specified above is less than thirty (30) days, a reply poperiod for reply is specified above, the maximum statutory period with the set or extended period for reply will, by statute, reply received by the Office later than three months after the mailing red patent term adjustment. See 37 CFR 1.704(b).	6(a). In no event, however, may a reply be t within the statutory minimum of thirty (30) da Ill apply and will expire SIX (6) MONTHS fror	imely filed ays will be considered timely. In the mailing date of this communication			
1)🛛	Responsive to communication(s) filed on 02 A	<u>oril 2003</u> .				
2a)□	This is a management of the second	s action is non-final.				
3) 🗌 Dispositi	Since this application is in condition for allowar closed in accordance with the practice under E on of Claims	ace except for formal	prosecution as to the merits is 453 O.G. 213.			
4)🖂	Claim(s) 1-10 is/are pending in the application.					
	4a) Of the above claim(s) is/are withdrawn from consideration.					
5)[Claim(s) is/are allowed.					
	Claim(s) <u>1-10</u> is/are rejected.					
	Claim(s) is/are objected to.					
	Claim(s) are subject to restriction and/or	election requirement				
Application	on Papers	olootion requirement.				
9)[] 1	he specification is objected to by the Examiner.					
ד 🔲 (10	The drawing(s) filed on is/are: a)☐ accepte	ed or b) objected to by the Exa	miner			
	Applicant may not request that any objection to the o	drawing(s) be held in abevance S	ee 37 CFR 1 85(a)			
11)[] T	he proposed drawing correction filed on is	s: a) approved b) disappro	oved by the Examiner			
	If approved, corrected drawings are required in reply	to this Office action.	Tod by the Examiner.			
12) T	he oath or declaration is objected to by the Exan	niner.				
Priority u	nder 35 U.S.C. §§ 119 and 120					
13)[🛛]	Acknowledgment is made of a claim for foreign p	riority under 35 U.S.C. & 119(a)-(d) or (f)			
a)[∑	All b)☐ Some * c)☐ None of:	,	, (a) or (i).			
•	1.⊠ Certified copies of the priority documents h	nave been received				
2	Certified copies of the priority documents h	lave been received in Application	on No			
	Copies of the certified copies of the priority	documents have been receive	d in this National Stage			
14)□ Ac	ee the attached detailed Office action for a list of	the certified copies not received	d.			
14) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).						
a) The translation of the foreign language provisional application has been received. 15) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.						
ttachment(s	s)	Monty under 35 U.S.C. 99 120	and/01/121.			
) Notice (of References Cited (PTO-892) of Draftsperson's Patent Drawing Review (PTO-948) tion Disclosure Statement(s) (PTO-1449) Paper No(s)	E\	(PTO-413) Paper No(s) atent Application (PTO-152)			
Patent and Trad						

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DETAILED ACTION

Election/Restrictions

1. Applicant's election without traverse of group I, claims 1-10 in Paper No. 8 is acknowledged.

Claim Rejections - 35 USC § 103

- 2. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 3. Claims 1-10 are rejected under 35 U.S.C. 103(a) as being unpatentable over Krantz et al., U.S. Patent Application Publication No. U.S 2002/0171825 A1.
- Krantz discloses a manufacturing method substantially as claimed.
- 4. Pertaining to claim 1, <u>Krantz</u> teaches a manufacturing method of a phase-shift mask, comprising: seeking a relationship of optical conditions of an exposure optical system used for exposure and a mask structure with displacement of a pattern to be transferred by exposure; finding said optical conditions and said mask structure that limit displacement of said pattern within a required range, taking manufacturing errors of the mask into consideration; examining the optical conditions and the mask structure obtained to determine whether they ensure a required exposure tolerance and a required focal depth; and executing fabrication of such a mask to obtain said mask structure when the result of the examination is acceptable [see Background of the Invention]. However, the terms "seeking a relationship of optical conditions", "examining the optical conditions" and "determine" are mental process steps. It would have been obvious to

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one of ordinary skill in the art that these mental process steps takes place in the <u>Krantz's</u> semiconductor process in the fabrication of phase shift mask.

- 5. Pertaining to claim 2, <u>Krantz</u> teaches the manufacturing method of a phase-shift mask according to claim 1 wherein said optical conditions include, at least, a numerical aperture [0015] and a partial coherence factor [0103].
- 6. Pertaining to claim 3, <u>Krantz</u> teaches the manufacturing method of a phase-shift mask according to claim 1 wherein said phase-shift mask is a Levenson phase-shift mask[0031].
- 7. Pertaining to claim 4, <u>Krantz</u> teaches the manufacturing method of a phase-shift mask according to claim 3 wherein said Levenson phase-shift mask is of a substrate-excavation-type, and said mask structure is regulated by the amount of excavation of a substrate [0095].
- 8. Pertaining to claim 5, <u>Krantz</u> teaches the manufacturing method of a phase-shift mask according to claim 1 wherein said Levenson phase-shift mask is of a phase-shifter-added-type, and said mask structure is regulated by the thickness of a phase shifter [see FIG. 18A].
- 9. Pertaining to claim 6, Krantz teaches a method of making a resist pattern through exposure using a phase-shift mask, comprising:
 seeking a relationship of optical conditions of an exposure optical system used for exposure and a mask structure of said phase-shift mask with displacement of a pattern to be transferred by exposure;
 finding said optical conditions and said mask structure that limit displacement of said pattern within a required range, taking manufacturing errors of the mask into consideration;

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examining the optical conditions and the mask structure
obtained to determine whether they ensure a required exposure
tolerance and a required focal depth; and
when the result of the examination is acceptable, fixing
said exposure optical system to the optical conditions selected,
then actually manufacturing said phase-shift mask having the mask
structure selected, and conducting exposure using said exposure
optical system and said phase-shift mask. However, Krantz fails to use the terms "finding", and
"examining". It would have been obvious to one of ordinary skill in the art that these mental
process steps takes place in the <u>Krantz's</u> semiconductor process in the fabrication of phase shift
mask.

- 10. Pertaining to claim 7, <u>Krantz</u> teaches the method of making a resist pattern according to claim 6 wherein said optical conditions include, at least, a numerical aperture and a partial coherence factor.
- Pertaining to claim 8, <u>Krantz</u> teaches the method of making a resist pattern according to claim 6 wherein said phase-shift mask is a Levenson phase-shift mask.
- 12. Pertaining to claim 9, <u>Krantz</u> teaches the method of making a resist pattern according to claim 8 wherein said Levenson phase-shift mask is of a substrate-excavation-type, and said mask structure is regulated by the amount of excavation of a substrate.
- 13. Pertaining to claim 10, <u>Krantz</u> teaches the method of making a resist pattern according to claim 8 wherein said Levenson phase-shift mask is of a phase-shifter-added-type, and said mask structure is regulated by the thickness of a phase shifter.

organization where this application or proceeding is assigned are 703-308-7722 for regular communications and 703-308-7721 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-0956.

> W. David Coleman Primary Examiner Art Unit 2823

WDC June 4, 2003